

Silicon PNP Epitaxial Planar Transistor (Complement to type 2SC2922)

Application : Audio and General Purpose

Absolute maximum ratings (Ta=25°C)

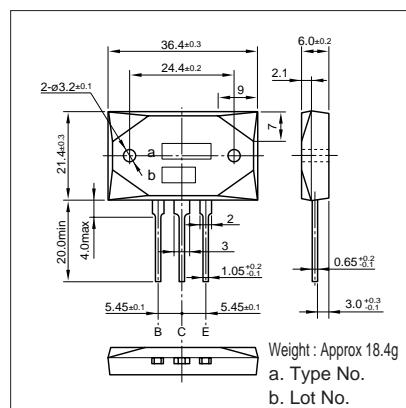
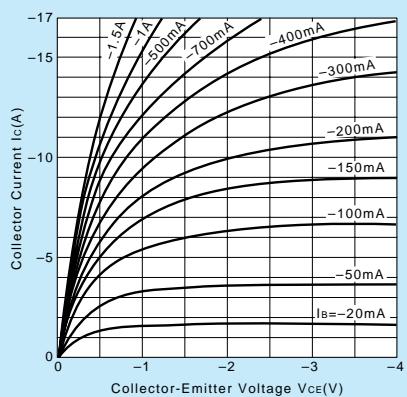
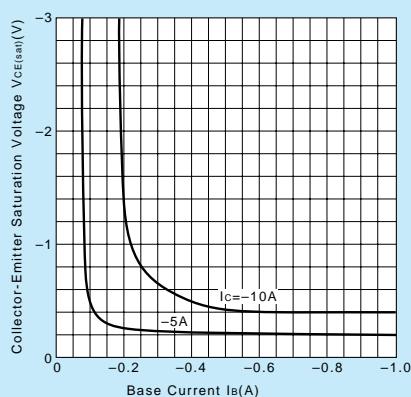
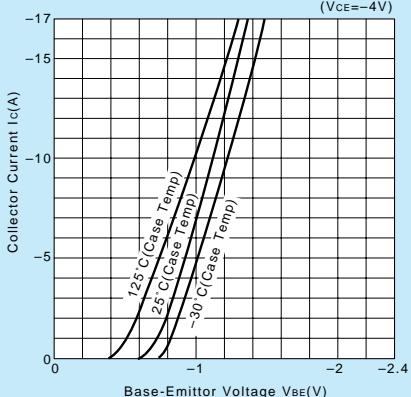
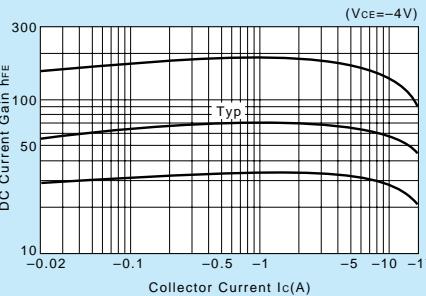
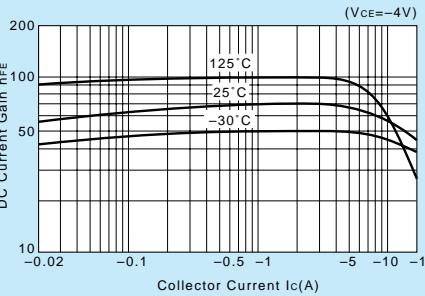
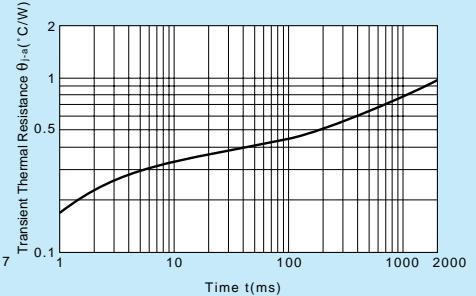
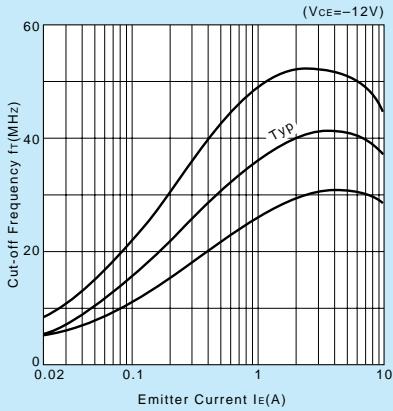
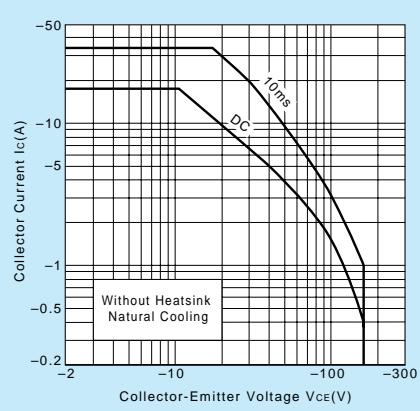
Symbol	2SA1216	Unit
V _{CBO}	-180	V
V _{CEO}	-180	V
V _{EBO}	-5	V
I _c	-17	A
I _b	-5	A
P _c	200(Tc=25°C)	W
T _j	150	°C
T _{tsg}	-55 to +150	°C

Electrical Characteristics (Ta=25°C)

Symbol	Conditions	2SA1216	Unit
V _{CBO}	V _{CB} =-180V	-100max	μA
I _{EBO}	V _{EB} =-5V	-100max	μA
V _{(BR)CEO}	I _c =-25mA	-180min	V
h _{FE}	V _{CE} =-4V, I _c =-8A	30min*	
V _{CE(sat)}	I _c =-8A, I _b =-0.8A	-2.0max	V
f _T	V _{CE} =-12V, I _e =2A	40typ	MHz
C _{OB}	V _{CB} =-10V, f=1MHz	500typ	pF

*h_{FE} Rank O(30 to 60), Y(50 to 100), P(70 to 140), G(90 to 180)**Typical Switching Characteristics (Common Emitter)**

V _{CC} (V)	R _L (Ω)	I _c (A)	V _{B2} (V)	I _{B1} (A)	I _{B2} (A)	t _{on} (μs)	t _{tsg} (μs)	t _f (μs)
-40	4	-10	5	-1	1	0.3typ	0.7typ	0.2typ

External Dimensions MT-200**I_c-V_{CE} Characteristics (Typical)****V_{CE(sat)}-I_B Characteristics (Typical)****I_c-V_{BE} Temperature Characteristics (Typical)****h_{FE}-I_c Characteristics (Typical)****h_{FE}-I_c Temperature Characteristics (Typical)****θ_{j-a}-t Characteristics****f_T-I_e Characteristics (Typical)****Safe Operating Area (Single Pulse)****P_c-T_a Derating**